Contents

This listing presents the papers in alphabetical order of the first author, subdivided according to the groupings "Solids and Materials" and "Surfaces, Interfaces, and Layer Structures". The author index that follows covers APPLIED PHYSICS A and B, and is presented in tabular form. The names are listed in alphabetical order in the first column. The second column the bibliographic data necessary to locate the paper. The issue is specified by the number separated from the volume number by a slash. The fourth column states the major PACS number so that the topic of the paper can be inferred by consulting the PACS listing on the left page.

SOLIDS and MATERIALS

Afifi M.A., Labib H.H.A., Abou El Ela A.H., Sharaf K.A.:
Threshold switching effects in AgTlSe2 and CuTlSe2 films.
Appl. Phys. A 46/2, 113-117 (1988) PACS: 72.20

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Silicone polymer deposition by CO2 laser induced decomposition of silane in the presence of methyl methacrylate.
Appl. Phys. A 46/4, 275-279 (1988) PACS: 82.50 68.55 78.65

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Photoenhanced deposition of silicon oxide thin films using a novel windowless internal nitrogen discharge lamp.
Appl. Phys. A 46/4, 243-248 (1988) PACS: 77.55 81.15

Benedetto G., Spagnolo R.:
Photoacoustic measurement of the thermal effusivity of solids.
Appl. Phys. A 46/3, 169-172 (1988) PACS: 43.35 81.70

Benkherourou O., Deville J.P.:
X-ray photoelectron spectroscopy of silicon oxynitride layers obtained by low-energy ion implantation.
Appl. Phys. A 46/2, 87-90 (1988) PACS: 73.40Q 79.60 61.70

Brandes G.R., Canter F.K., Horsky T.N., Mills A.P. Jr.:
Demonstration of positron re-emission microscopy using an immersion objective.
Appl. Phys. A 46/4, 335-338 (1988) PACS: 07.80 78.70 66.55

Cerdeira F., Torriani I., Motisuke P., Lemos V., Decker F.:
Optical and structural properties of polycrystalline CdSe deposited on titanium substrates.
Appl. Phys. A 46/2, 107-112 (1988) PACS: 78.20 61.10 81.15

Dünnwald J., Winter J., Vietzke E., Otto A.:
Raman spectroscopy of carbonization films and carbonaceous limiters in fusion vessels.
Appl. Phys. A 46/2, 91-96 (1988) PACS: 52.40H 61.40 78.30

Fernández P., Remon A., Garcia J.A., Llopis J., Piqueras J.:
Localized luminescence in ZnO:Mn ceramics.
Appl. Phys. A 46/1, 1-3 (1988) PACS: 78.55H 78.60 81.40

Garcia B.J., Martinez J., Piqueras J., Castano J.L., Minoz-Yagüe A.:
Ge diffusion into GaAs by pulsed laser irradiation.
Appl. Phys. A 46/3, 191-196 (1988) PACS: 61.70T 79.20 72.80

Garrido-Suarez C., Braichotte D., Bergh H. van den:
Searching for optimum conditions in the laser writing of small ohmic contacts.
Appl. Phys. A 46/4, 285-290 (1988) PACS: 42.60 81.10 85.40

Gupta P.K., Chopra K.L.:
Plasma-processed obliquely deposited Bi-Ge-Se and Ag/Bi-Ge-Se films as resist materials.
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Orthorhombic NaREGeO4 crystals with Nd3+ ions; structure and formation, luminescence properties and stimulated emission.
Appl. Phys. A 46/3, 173-183 (1988) PACS: 42.55R 61.10 61.50 61.60

Kunst M., Müller G., Schmidt R., Wetzel H.:
Surface and volume decay processes in semiconductors studied by contactless transient photoconductivity measurements.
Appl. Phys. A 46/2, 77-85 (1988) PACS: 72.40 73.20

Lee W.-Y., Wang W.-S.:
Approximation to the two-step diffusion profile by a series of Gaussian functions.
Appl. Phys. A 46/4, 281-283 (1988) PACS: 61.70W 66.30 61.70

Liberts G., Eyett M., Bäuerle D.:
Direct laser writing of superconducting patterns into thesuperconducting ceramic Y-Ba-Cu-O.
Appl. Phys. A 46/4, 331-334 (1988) PACS: 74.70V 42.60 82.65

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Single-wafer optical processing of semiconductors: Thin insulator growth for integrated electronic device applications.
Appl. Phys. A 46/4, 255-273 (1988) PACS: 73.60 77.55 81.10

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Relaxation oscillators made of bridge-type Josephson contacts.
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Mechanism for nonlinear I-V behaviour and temperature dependence of threshhold switching in Se-Te-Sn system.
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Photocurrents in p-n Si diodes under high intensity (pulsed-laser) illumination: Quantum yields and kinetic evaluation.
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Schorn R.P., Zaki Ewiss M.A., Hintz E.:
Velocity distributions of copper and lithium atoms sputtered from a Cu/Li alloy measured with laser induced fluorescence.
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Diffusion of selenium and tellurium in silicon.
Appl. Phys. A 46/3, 159-163 (1988) PACS: 66.30

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Low-temperature fabrication of silicon nitride films by ArF excimer laser irradiation.
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Lattice imaging study of in-depth disordering of Si-implanted GaAs.
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Nitrogen-oxygen complexes in Czochralski silicon.
Appl. Phys. A 46/2, 73-76 (1988) PACS: 61.70 78.30

Wieder T., Thoma K., Gärtner H.:
New scattering formula for the analysis of X-ray line broadening by composition profiles.
Appl. Phys. A 46/3, 165-167 (1988) PACS: 61.10D 78.70

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Macroscopic short-time electrodynamics for conductors.
Appl. Phys. A 46/1, 17-23 (1988) PACS: 03.50D 41.10 42.90

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Compounds in mixed phase CeBa2Cu3Oy and TbBa2Cu3Oy systems.
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The structure and defect structure of high Tc superconducting materials in the system Tl-Ba-Ca-Cu-O.
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The influence of substrate material and annealing procedure on the properties of superconducting thin films.
Appl. Phys. A 46/3, 215-220 (1988) PACS: 73.00 74.00 81.00

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Influence of surface roughness on adsorbate mobility. Cross-correlation measurements of potassium coadsorbed with nickelon the W(112) plane.
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Chemical etching of silicon by CO2-laser-induced dissociationof NF3.
Appl. Phys. A 46/1, 39-50 (1988) PACS: 82.50E 82.65 82.80

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Appl. Phys. A 46/4, 339-342 (1988) PACS: 73.60K 74.70 81.15

Hwu J.-G., Fu S.-L.:
The radiation hardness property of dry oxide grown by postoxidation cooling in oxygen ambient.
Appl. Phys. A 46/3, 221-227 (1988) PACS: 73.00

Jabr I.J., Al-Saleh K.A., Saleh N.S.:
Ion-beam induced mixing of Cu/Au bilayer thin film (kinematics and formation of solid solutions).
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New stable microwave plasma passivated a-Si MIS cells with high open circuit voltage.
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Analysis of rapid dry oxidation of silicon.
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Thermochemical dry etching of single crystal ferrite by laser irradiation in CCl4 gas atmosphere.
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Tendeloo G. van, Zandbergen H.W., Landuyt J.van, Amelinckx S.:
The deffect structure of the high-Tc superconductors in the system Bi-Ca-Sr-Cu-O.
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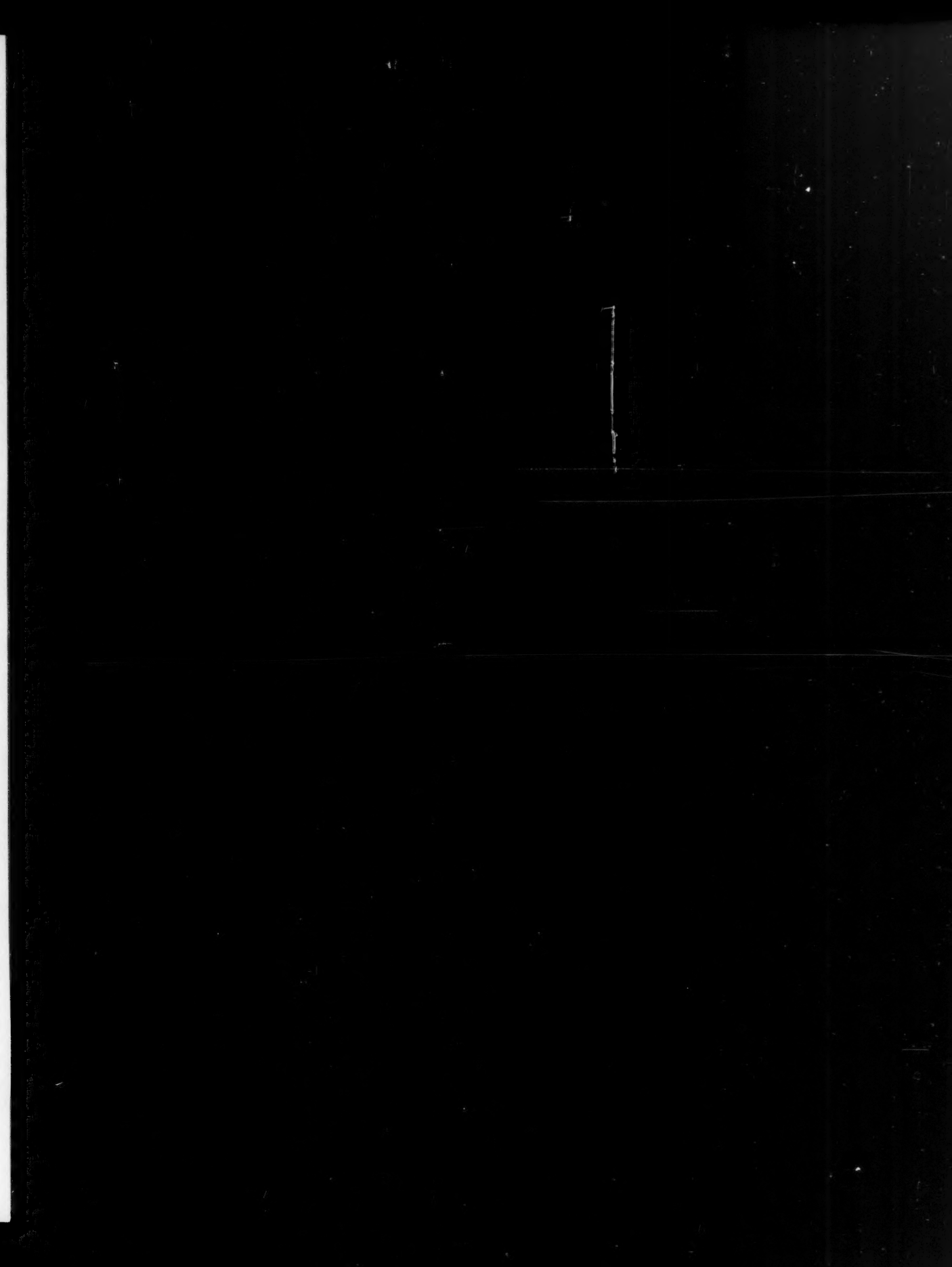
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